RENESAS

RJK2511DPK

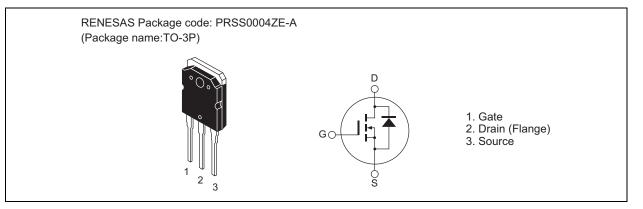
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1486-0400 Rev.4.00 Nov 27, 2007

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	250	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	ID	65	А
Drain peak current	Note1 I _{D (pulse)}	200	А
Body-drain diode reverse drain current	I _{DR}	65	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	200	А
Avalanche current	I _{AP} ^{Note3}	22	А
Avalanche energy	E _{AR} ^{Note3}	30.2	mJ
Channel dissipation	Pch Note2	200	W
Channel to case thermal impedance	θch-c	0.625	°C/W
Channel temperature	Tch	150	٥°
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25°C

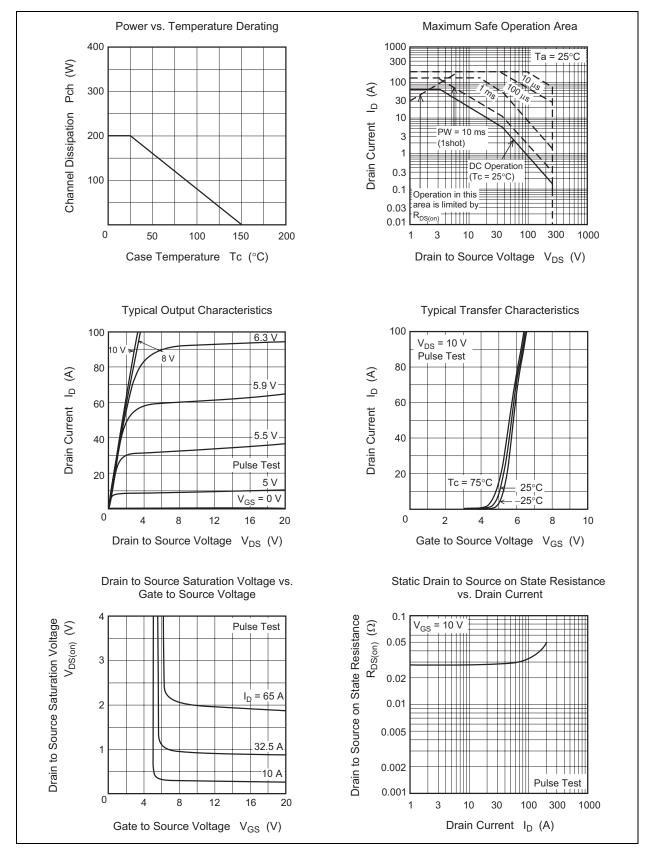
3. STch = 25° C, Tch $\leq 150^{\circ}$ C

Electrical Characteristics

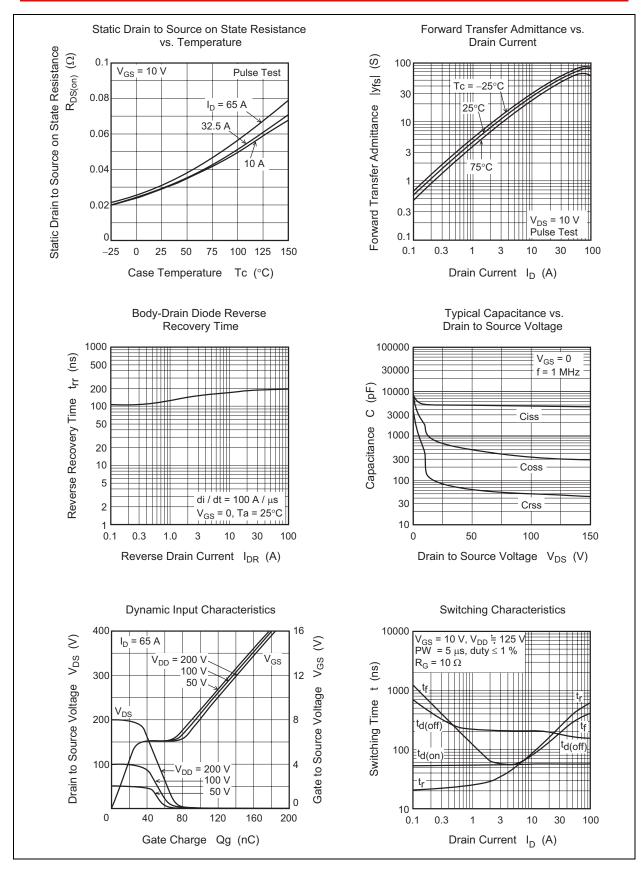
						(Ta = 25°C)
Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	250	—		V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 250 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}		—	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	yfs	30	51	_	S	$I_D = 32.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Static drain to source on state resistance	R _{DS(on)}	_	0.028	0.034	Ω	$I_D = 32.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	4900	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	690	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	—	85		pF	
Turn-on delay time	t _{d(on)}	—	52		ns	I _D = 32.5 A
Rise time	tr		200		ns	$V_{GS} = 10 V$ $R_L = 3.9 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t _{d(off)}	_	160	_	ns	
Fall time	t _f	_	150	_	ns	
Total gate charge	Qg	_	120	_	nC	$V_{DD} = 200 V$ $V_{GS} = 10 V$ $I_D = 65 A$
Gate to source charge	Qgs	_	28	_	nC	
Gate to drain charge	Qgd	—	51	_	nC	
Body-drain diode forward voltage	V _{DF}	—	0.93	1.50	V	$I_F = 65 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t _{rr}		200		ns	$I_F = 65 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$
Body-drain diode reverse recovery	Q _{rr}	_	1.5	_	μC	
charge						

Notes: 4. Pulse test

Main Characteristics

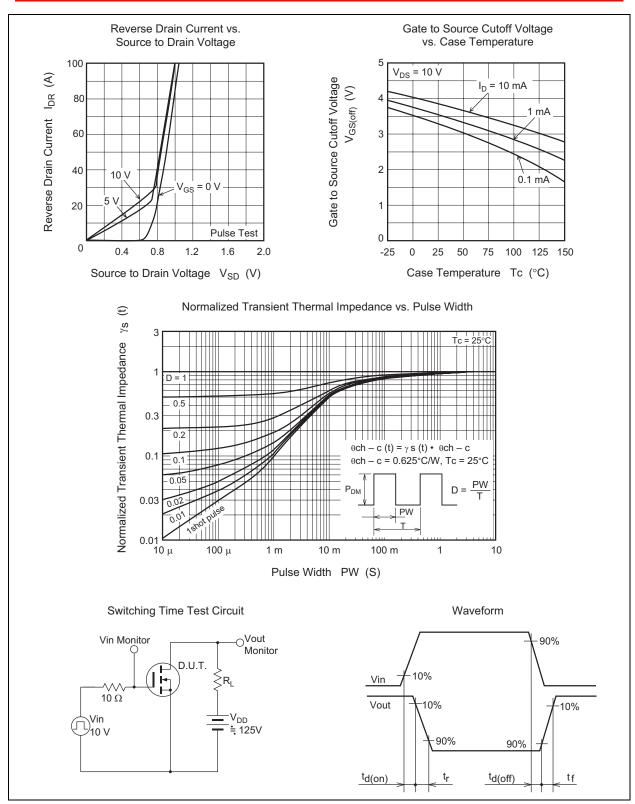


RENESAS



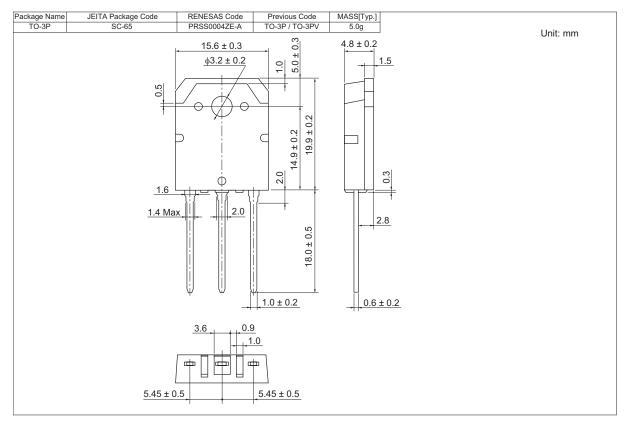
REJ03G1486-0400 Rev.4.00 Nov 27, 2007 Page 4 of 6

RENESAS



RENESAS

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK2511DPK-00-T0	360 pcs	Box (Tube)

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- <section-header>

 Image: States

 Present States

 States

 Present State



http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd. 1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510